

THz Detectors

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Short Bunches in Accelerators- USPAS, Boston, MA 21-25 June 2010

Overview



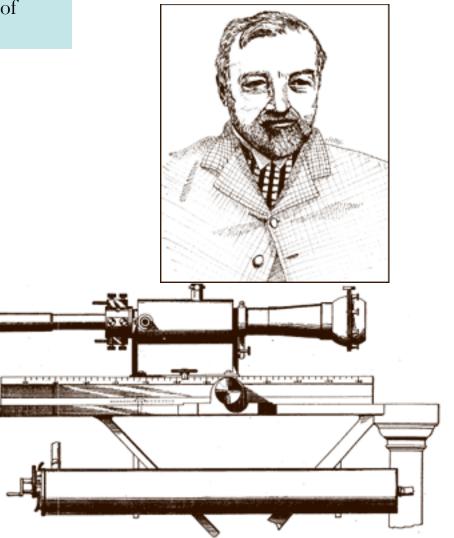
- Bolometers
- Pyroelectric detectors
- Diodes
- Golay Cell

Bolometers



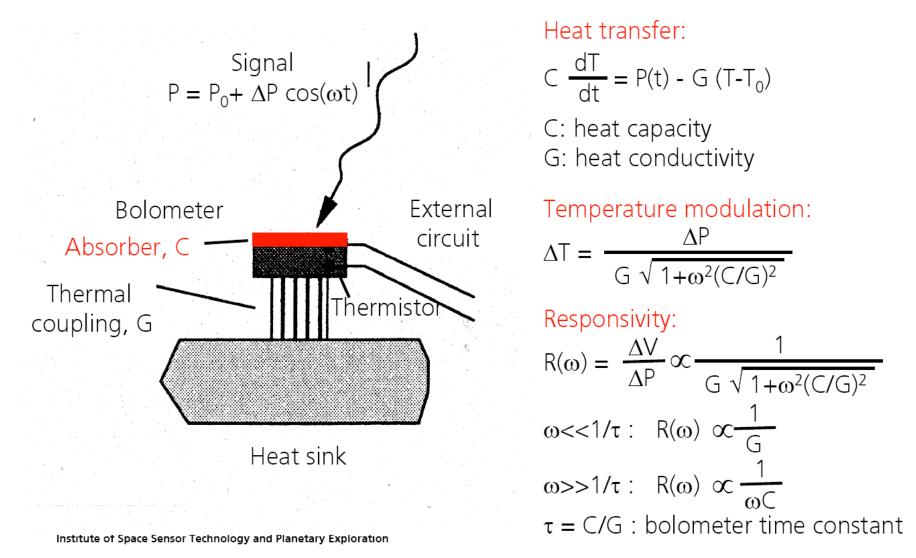
Bolometer: ORIGIN late 19th cent.: from Greek bolē 'ray of light' + **-meter**

In 1878 Samuel Pierpont Langley invented the bolometer, a radiant-heat detector that is sensitive to differences in temperature of one hundredthousandth of a degree Celsius (0.00001 C). Composed of two thin strips of metal, a Wheatstone bridge, a battery, and a galvanometer (an electrical current measuring device), this instrument enabled him to study solar irradiance (light rays from the sun) far into its infrared region and to measure the intensity of solar radiation at various wavelengths.



Bolometer principle





Far-IR Silicon bolometer



•Spectral response: 2-3000 micron

•Operating temperature:

4.2-0.3 deg-K

•Responds only to AC signal within detector bandwidth (may need a chopper.)

T _o (K)	4.2	1.2	0.3		
G (w/K)	1 x 10 ⁻⁵	1 x 10 ⁻⁷	1 x 10 ⁻⁸		
F _o (Hz)	> 8 x 10 ²	> 5 x 10 ²	> 1 x 10 ³		
NEP (w/Hz1/2)	1 x 10 ⁻¹³	3 x 10 ⁻¹⁵	2.4 x 10 ⁻¹⁶		
Table 1-2: Theoretical Performance of minimum					

area (A = 6.25 x 10-4 cm2) bare Si bolometers



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Pyroelectric Detectors

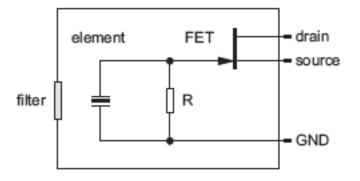


•Ferroelectric materials such as TGS or Lithium Tantalate, exhibit a large spontaneous electrical polarisation which has varies with temperature.

- •Observed as an electrical signal if electrodes are placed on opposite faces of a thin slice of the material to form a capacitor.
- •Creates a voltage across the capacitor for a high external impedance
- •Only sensitive to AC signals (I.e. time-varying)
- Room temperature operature
- •Small detector area can give fast thermal response time. (<1 microsec)

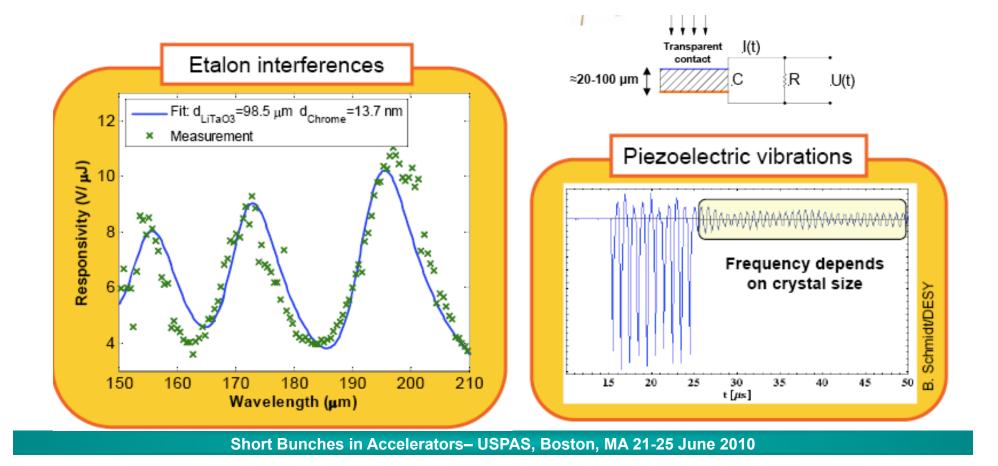
NEP (W/Hz1/2, BW-1Hz) =1.1 x 10-9 Responsivity (V/W)=3.7 x 105





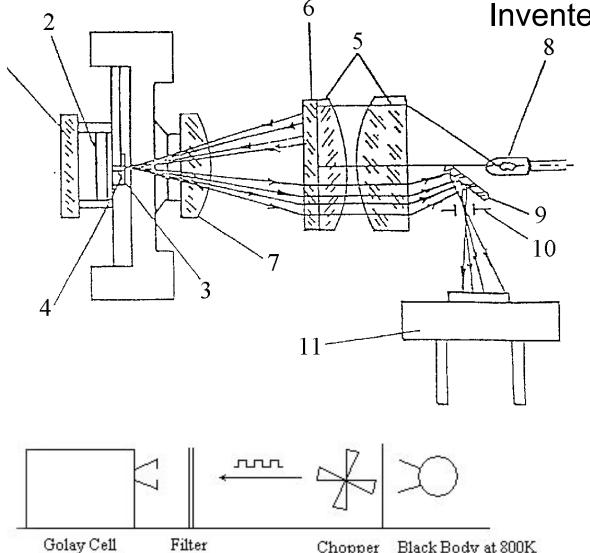
Pyroelectric Detectors

- Pyroelectric effect sensitive only to heat (not wavelength)
- Wavelength selection made with window material
- Sensitive to piezoelectric noise (vibrations=noise signal)



Golay Cell





Chopper

Invented by M.J.E.Golay in 1947

A modulated signal (1) is incident upon the semi-transparent film (2). This heats the gas in the chamber and distorts the membrane forming the wall of the chamber. An LED (8) sends a signal onto the mirrored back surface of the chamber containing the absorbing membrane. The modulated signal appears as a modulated optical signal.

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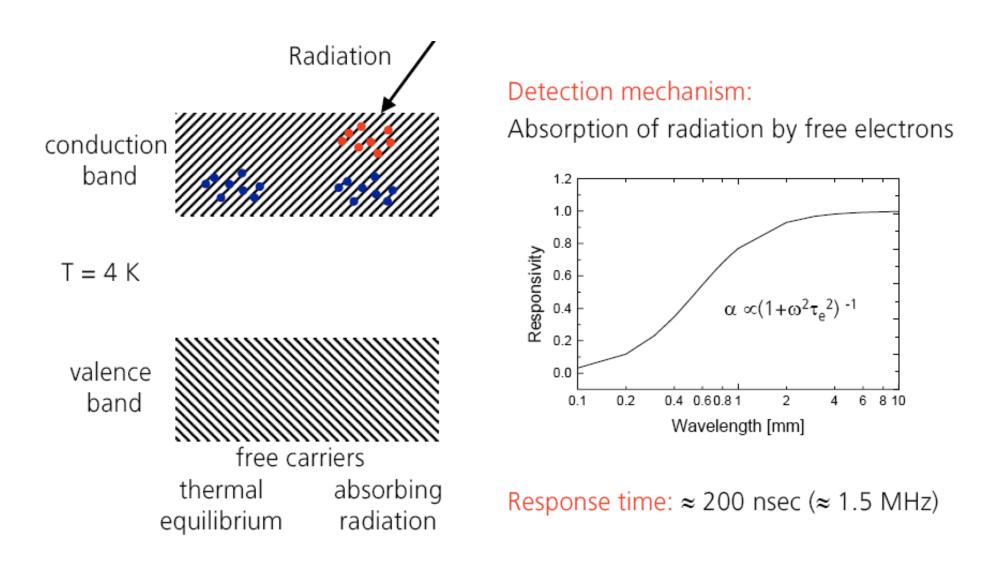
Black Body at 800K

Golay Cell

- •Operating temperature = 300K
- •Wavelength range (polyethylene window) = 20 to $1000\mu m$
- •Optical responsivity at $15Hz \ge 100 \text{ kV/W}$
- •Optical NEP at 15Hz : < 100 pWatt.Hz-1/2
- •Speed (-3 dB) = 25Hz
- •Detector weight = 1kg
- •Detector dimensions I=140mm, w=65mm, h=90mm
- •Connecting lead length \cong 1m

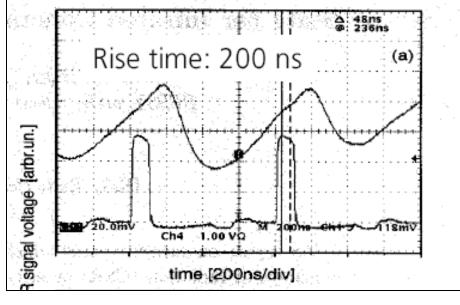


Indium Antimonide (InSb) Detectors



InSb with CSR signals





Rise time: ≈200 nsec

Decay time: > 400 nsec

Resolution of single bunches within a train of bunches is not possible.

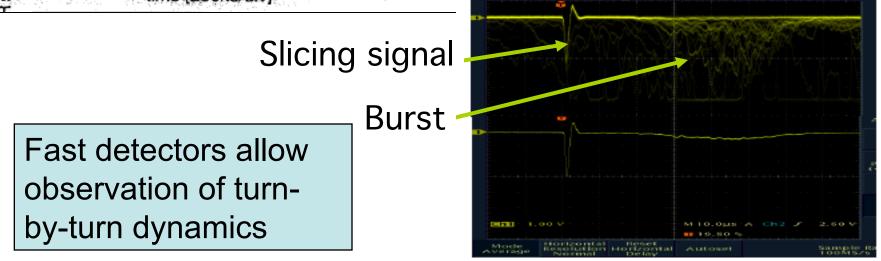
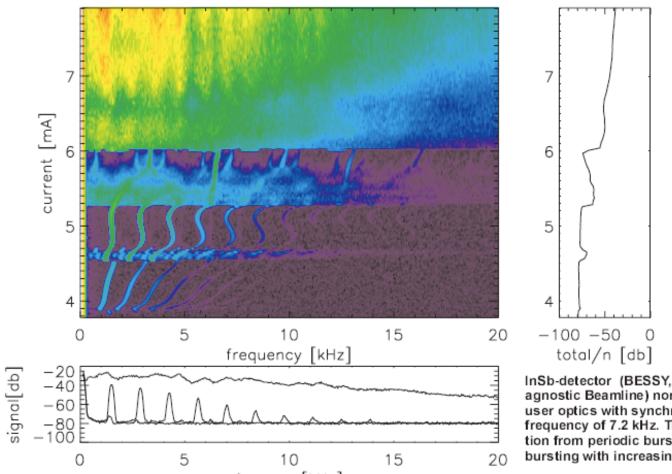
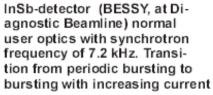


Figure 7: Scope tracks of the seeded burst signal at the fast detector. Scales: 10 µs/div and 1V/div

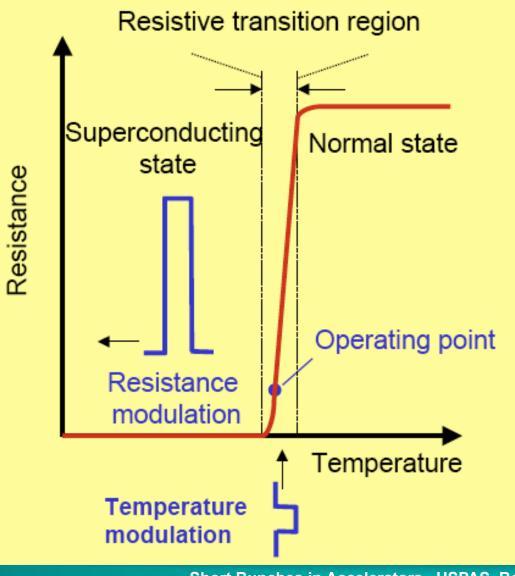
Frequency domain response

detecting electron beam instabilities and thresholds. Transition of periodic to chaotic bursting in single bunch mode





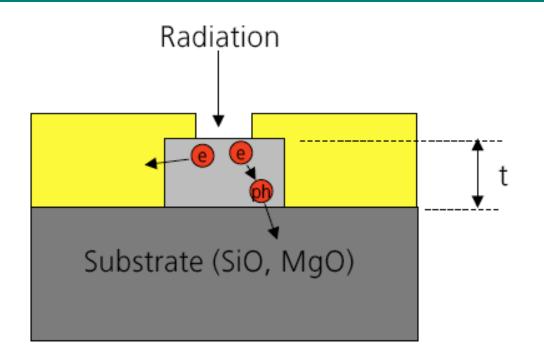
Superconducting Hot Electron Bolometer

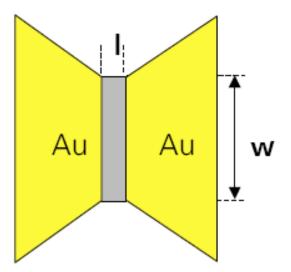


Detector operates at superconducting transition region. Small temperature modulation gives large resistance modulation.

HEB dimensions





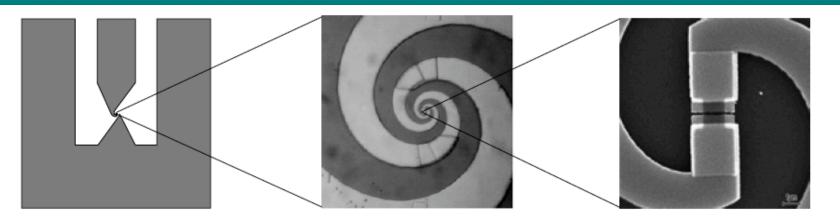


Time scales (NbN):

 $\tau_{e-e} \approx 2 \text{ ps}$ $\tau_{e-ph} \approx 15 \text{ ps}$ $\tau_{esc} \approx 25-50 \text{ ps}$ (3.5 nm film) Dimensions:

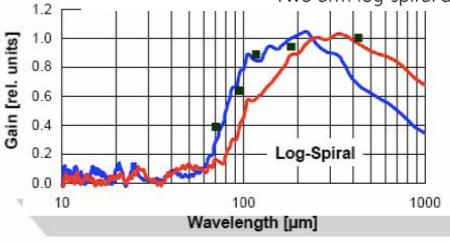
l: 0.2 - 1.0 μm w: 1 - 4 μm t: 3.5 nm

HEB Antenna and mixer



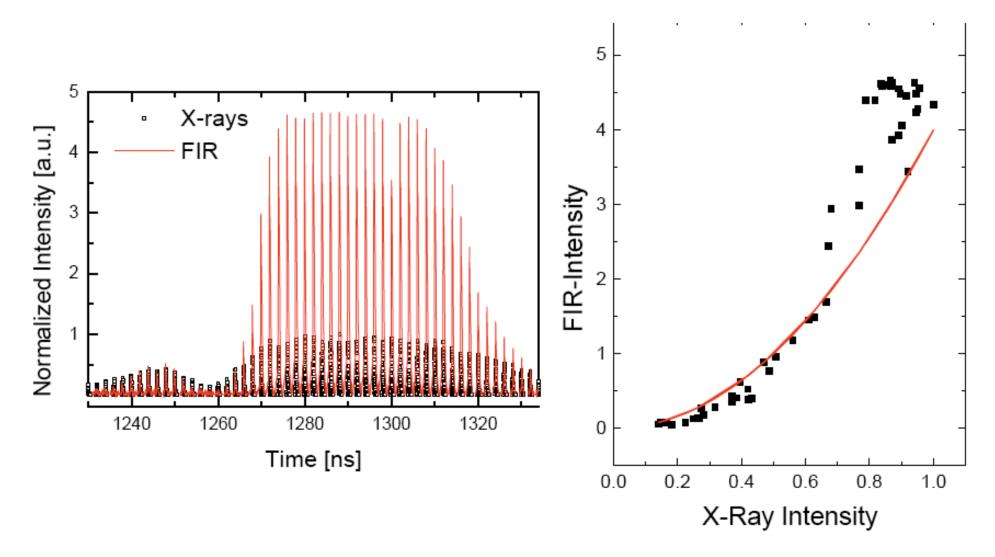
- NbN film: 3.5 nm thick (dc reactive magnetron sputtering)
- Transition temperature: 9 K, width: ≈ 0.5 K
- Si substrate: > 10 k Ω cm







Bessy Beam signals



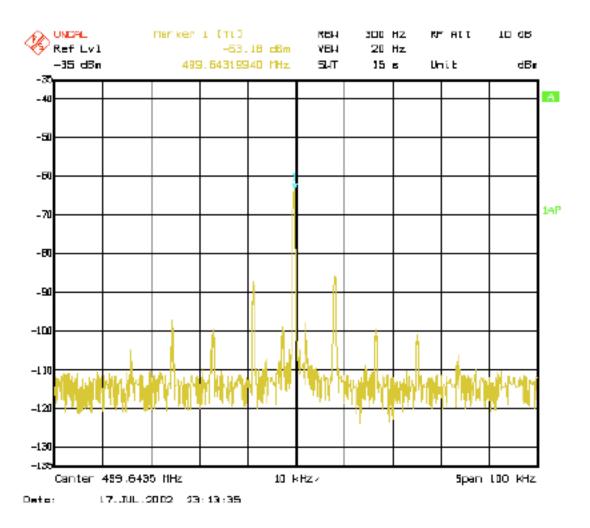
HEB Response time 0.09 0.08 400 ps 0.07 0.06 Intensity [a.u.] 0.05 0.04 0.03 When the way was a way and a wa 0.02 BESSY II: tune 2.3 KHz, 9.2 mA 0.01 HEB: 8.0 K, 2.1 mV, 164.1 µA 0.00 500 1000 1500 2000 0 Time [ps] Measurement: ≈ 50 ps $\tau_{\rm rise} \approx 50 \ \rm ps$ 0.035 Detector: Intensity [a.u.] 0.030 $\tau_{e\text{-}e} \approx$ 2 ps $\tau_{e\text{-ph}} pprox$ 25 ps 0.025 $\tau_{electr} \approx 35 \text{ ps}$ BESSY II: tune 2.3 KHz, 5.8 mA HEB: 8.0 K, 3.1 mV, 138.5 µA 0.020 Electron bunch: $\tau_{\text{FWHW}} \approx 10 \text{ ps}$ 0.015 50 100 150 200 n Time [ps] **Short Bunches in**

Frequency response



500 MHz component of HEB signal.

Indicates sufficient resolution for 2 nsec bunch spacing. Sensitive to multibunch dynamics affecting CSR signal.



Diode Detectors



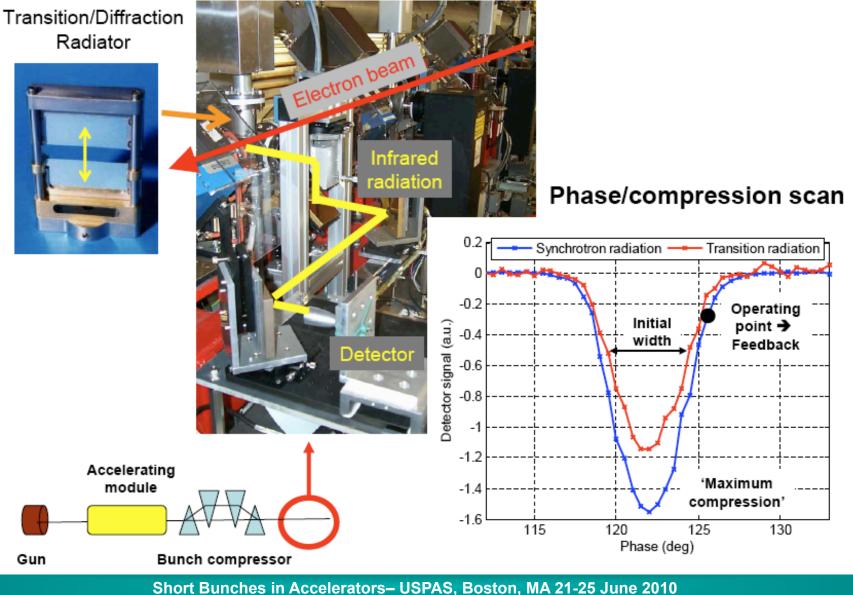


Virginia Diodes, Inc., Cha

Model Number	DXP-06
Frequency band and range (GHz)	D 110-170
Video voltage (mV at -20 dB input) (typ)	5
Video sensitivity (mV/mW) (min into 1 M Ω)	150
Flatness (dB) (typ)	±3.0
TSS at 1 kHz (bw 40 Hz, dBm) (typ) ^{^1}	-40
Video bandwidth (MHz) (typ) ²	10
Operating RF input power (dBm, CW max)	+16
Absolute max rating (dBm)	+20

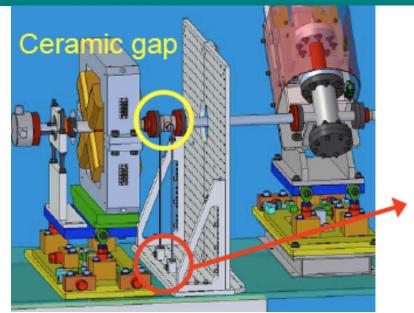
Band	WR-	(GHz)	Comment	
L	650	1.1-1.7	Long wave	
R	430	1.7-2.6		
S	284	2.6-3.95	Short wave	
H (G)	187	3.95-5.85		
С	137	5.85-8.2	Comprise between S and X	
W (H)	112	7.05-10		
Х	90	8.2-12.4	Used in WWII for fire control, X for cross as in cross-hair.	
Ku	62	12.4-18	Kurz-under	
K	42	18-26.5	Kurz (German word for short)	
Ka	28	26.5-40	Kurz-above	
Q	22	33-50	VDI: WR22x2 is a frequency doubler to 32-55 GHz.	
U	19	40-60	VDI: D55v2 covers ~ 47-58 GHz.	
V	15	50-75	VDI: WR15x2 is a frequency doubler to 50-75 GHz.	
E	12	60-90	VDI: WR12x2b is a frequency doubler to 60-90 GHz.	
W	10	75-110	VDI: WR10x2c, D90, D100	
F	8	90-140	VDI: WR8x3 is a frequency tripler to 90-140 GHz.	
D	6.5	110-170	VDI: WR6.5SHM is a subharmonic mixer to 110-170 GHz.	
G	5.1	140-220	VDI: WR5.1DD, WR5.1ZBD, WR5.1x2, WR5.1x3, D200	
	4.3	170-260	VDI: WR4.3x2, WR4.3x3, WR4.3x6, WR4.3SHM, D240	
	3.4	220-325	VDI: WR3.4x2, WR3.4x3, WR3.4SHM, WR3.4ZBD	
	2.8	265-400	VDI band: WR2.8x2, WR2.8x3, WR2.8DD, WR2.8HM	
	2.2	330-500	VDI band: WR2.2x2, WR2.2x3, WR2.2x5, D400, T438	
	1.9	400-600	VDI band: WR1.9x2, WR1.9x3, WR1.9x5, D480	
	1.5	500-750	VDI band: WR1.5ZBD (zero bias detector)	
	1.2	600-900	VDI band: WR1.2x3, WR1.2x5, WR1.2SHM, T738	
	1.0	750-1000	VDI band: WR1.0x3	
	0.65	1100-1700	VDI band: WR0.65x3, WR0.65x5	

FLASH Bunch compression monitor



SLAC bunch shape monitor



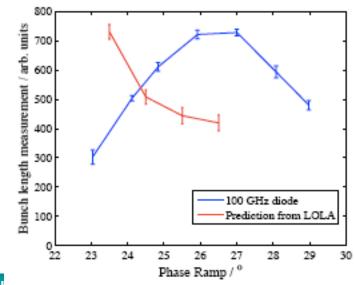


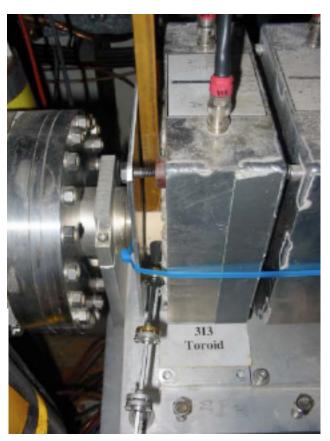


Tunerless Design
No bias require d
NEP: 1E-10 W/Hz^0.5 (typ.)
TSS: -44 dBm (typ.)
TSS measured with 30 kHz video bandwidth



Virginia Diodes, Inc., Ph:434.297.325





MA 21-25 June 2010

Wire Grid Polarizers

